RF POWER FIELD-EFFECT TRANSISTOR

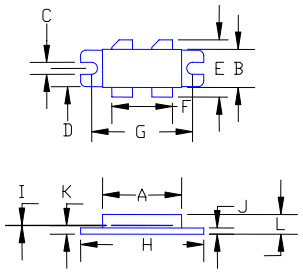
DESCRIPTION:

The **ASI UFT150-28** is a N-Channel Enhancement-Mode Push Pull MOSFET, Designed for FM, and TV Solid State Transmitter Applications up to 500 MHz.

MAXIMUM RATINGS

I_D	26 A
V_{DSS}	65 V
P_{DISS}	400 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.44 °C/W

PACKAGE STYLE .400 BAL FLG



	MINIMUM INCHES/MM	MAXIMUM INCHES/MM
A	.850/21.59	.870/22.10
B	.395/10.03	.407/10.34
C	.125/3.18	
D	.1925/4.889	
E	.580/14.73	.620/15.75
F	.660/16.76	
G	1.090/27.69	1.105/28.07
H	1.335/33.91	1.345/34.16
I	.003/0.08	.007/0.18
J	.060/1.52	.070/1.78
K	.082/2.08	.097/2.46
L		.205/5.21

1 = DRAIN 2 = DRAIN(2) 3 = GATE(1)
4 = GATE(2) 5 = SOURCE (1&2) -CASE

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
$V_{(BR)DSS}$	I_D = 50 mA	V_{GS} = 0 V		65			V
I_{DSS}	V_{DS} = 28 V	V_{GS} = 0 V				2.5	mA
I_{GSS}	V_{DS} = 0 V	V_{GS} = 20 V				1.0	µA
$V_{GS(th)}$	I_D =100 mA	V_{DS} = 10 V		1.0	3.0	6.0	V
$V_{DS(on)}$	I_D = 5.0 A	V_{GS} = 10 V				1.5	V
g_{fs}	I_D = 2.5 A	V_{DS} = 10 V		2.0	3.0		mhos
C_{iss} C_{oss} C_{rss}	V_{DS} = 28 V	V_{GS} = 0 V	f = 1.0 MHz		180 200 20		pF
G_{ps} η ψ	V_{DD} = 28 V	I_{DQ} = 2 X 100 mA	P_{OUT} = 200 W f = 225 MHz	12 55 10:1	14 65 ---		dB % ---